

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	110	electron beam with vapor same ionize\$ and ("118" or "427").clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/17 06:57
L2	184	bias voltage with surface same vapor deposit\$3	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/17 07:52
L3	489	bias voltage with (surface or substrate) same vapor deposit\$3	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/17 07:54
L4	129	bias voltage with (surface or substrate) same vapor deposit\$3 and ("118" or "427"). clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/17 07:55
S1	7	(Itoh and Higuchi and Sakai and Honda and Takai and Okazaki and Inaba).in.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 09:50
S2	888313	Matsushita.as.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 09:59
S3	576436	(Matsushita Electric).as.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 09:59
S4	34558	(Matsushita Electric Industrial).as.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 09:59
S5	23206	Matsushita.as. and thin film	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 09:59

S6	1358	Matsushita.as. and thin film and electron beam	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 10:00
S7	528	Matsushita.as. and thin film and electron beam and heating	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 10:19
S8	15	Matsushita.as. and thin film and electron beam and resistive heating	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 10:19
S9	2	jp-01117208-\$.did.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 10:22
S10	28	((118/726 or 118/715 or 118/723).ccls. and ionizing and resistive heating	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 10:57
S11	38	((118/726 or 118/715 or 118/723).ccls. and (electron beam or EB) and resistive heating	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 11:00
S12	113	((118/726 or 118/715 or 118/723).ccls. and (vapor ADJ5(electron beam or EB))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 11:05
S13	127	((118/726 or 118/715 or 118/723).ccls. and ((vapor or gas) ADJ5 (electron beam or EB))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 11:06
S14	82	((118/726 or 118/715 or 118/723).ccls. and ((vapor or gas) ADJ5 (electron beam or EB)) and heating	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 11:07
S15	1	("5436035").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/03/11 11:26
S16	2	(jp-58123867-\$.).did.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 16:30

S17	11	apparatus and ((resistance heating and electron beam) evaporation source)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 15:53
S18	3	(apparatus or machine or device) and ((resistance heating and electron beam) evaporation source) and nozzle	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 16:01
S19	14	(apparatus or machine or device) and ((resistance heating and electron beam) evaporation source)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 16:06
S20	33	(apparatus or machine or device) and ((resistance ADJ2 heating and electron ADJ2 beam) ADJ2 evaporation ADJ2 source)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 16:10
S21	5	(apparatus or machine or device) and ((resistance ADJ2 heating and electron ADJ2 beam) ADJ2 evaporation ADJ2 source) and nozzle	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 16:12
S22	9	(apparatus or machine or device) and ((resistance ADJ2 heating and electron ADJ2 beam) ADJ2 evaporation ADJ2 source) and (bias or negative)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 16:23
S23	20	(wada and nakagawa and hananaka).in.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 07:27
S24	9	(apparatus or machine or device) and ((resistance ADJ2 heating and electron ADJ2 beam) ADJ2 evaporation ADJ2 source) and (bias or negative or minus)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 07:38
S25	15	(apparatus or machine or device) and ((resistance ADJ2 heating and electron ADJ2 beam) ADJ4 evaporation ADJ2 source) and (bias or negative or minus)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 07:48

S26	239	(apparatus or machine or device) and ((resistance ADJ2 heating or electron ADJ2 beam) ADJ4 evaporation ADJ2 source) and (bias or negative or minus)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 07:49
S27	212	(apparatus or machine or device) and ((resistance ADJ2 heating or electron ADJ2 beam) ADJ2 evaporation ADJ2 source) and (bias or negative or minus)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 07:49
S28	9	(apparatus or machine or device) and ((resistance ADJ2 heating or electron ADJ2 beam) ADJ2 evaporation ADJ2 source) and ((bias or negative or minus) adj2 (source or device))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 07:50
S29	1	("4394210").PNL	US-PGPUB; USPAT; USOCR	OR	OFF	2008/03/13 07:55
S30	65	(electron adj2 beam adj2 evaporation) and (resistance adj2 heating adj2 evaporation) and ((negative or bias) adj3 voltage)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 08:07
S31	7	(apparatus or machine or device) and ((resistance heating and electron beam) evaporation source) and (nozzle or tube or port)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 10:05
S32	12	(apparatus or machine or device) and ((resistance ADJ2 heating and electron ADJ2 beam) ADJ2 evaporation ADJ2 source) and (nozzle or tube)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 10:09
S33	1301	vacuum near2 (container or chamber) and electron near2 beam and resistance near2 heating	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:06
S34	261	vacuum near2 (container or chamber) and electron near2 beam and resistance near2 heating and bias	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:07

S35	45	vacuum near2 (container or chamber) and electron near2 beam and resistance near2 heating and bias and nozzle	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:07
S36	63	vacuum near2 (container or chamber) and electron near2 beam and resistance near2 heating and (118/726 or 118/715 or 118/723).cls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:13
S37	1	("20020001733").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/07/16 11:18
S38	149	(118/726 or 118/715 or 118/723).cls. and electron and resistive heating	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:32
S39	12	(118/726 or 118/715 or 118/723).cls. and electron same resistive same vacuum	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:33
S40	3343	ion\$6 adj2 assisted with deposition	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:45
S41	127	ion\$6 adj2 assisted with deposition and "118". clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:46
S42	42	(shinohara toshiro).in.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 16:09
S43	1080	electron beam with gas and ("118" or "427"). clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 16:11
S44	24	electron beam with gas with path and ("118" or "427").clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 16:11

S45	98	electron beam with gas same ionize\$ and ("118" or "427").clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 16:13
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